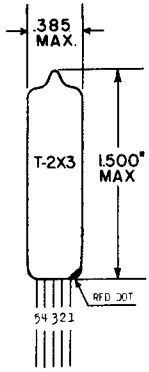
TUNG-SOL

OUTLINE DRAWING
JEDEC 2-1



GLASS BULB
BULB ENTIRELY COATED WITH METALLIC SHIELD CONNECTED TO LEAD #3

COLOR DOT IS ADJACENT TO LEAD #1

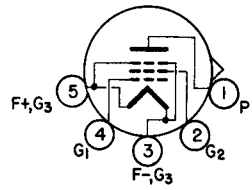
PENTODE

SUBMINIATURE
FILAMENTARY TYPE

FOR RF APPLICATIONS

ANY MOUNTING POSITION

BASING DIAGRAM



BOTTOM VIEW
5 FLEXIBLE IN-LINE TINNED LEADS 0.016" DIA. 0.048" CENTER-TO-CENTER

THE 6611 IS A FILAMENTARY TYPE, FULLY SHIELDED PENTODE IN THE T-2 X 3 SUBMINIATURE CONSTRUCTION. IT IS DESIGNED FOR USE IN RF APPLICATIONS WHERE ECONOMY OF SPACE, WEIGHT AND BATTERY DRAIN IS ESSENTIAL.

DIRECT INTERELECTRODE CAPACITANCES

GRID 1 TO PLATE	MAX. 0.008	pf
INPUT	4.0	pf
OUTPUT	4.0	pf

FILAMENT CHARACTERISTICS AND RATINGS

ABSOLUTE MAXIMUM VALUES – SEE EIA STANDARD RS-239

AVERAGE CHARACTERISTICS	1.25	VOLTS	20	MA
LIMITS OF APPLIED VOLTAGE			1.25 ± 0.35	VOLTS

MAXIMUM RATINGS

ABSOLUTE MAXIMUM VALUES – SEE EIA STANDARD RS-239

PLATE VOLTAGE	50	VOLTS
GRID 2 VOLTAGE	50	VOLTS
PLATE DISSIPATION	0.10	WATT
GRID 2 DISSIPATION	0.02	WATT
TOTAL CATHODE CURRENT	1.9	MA

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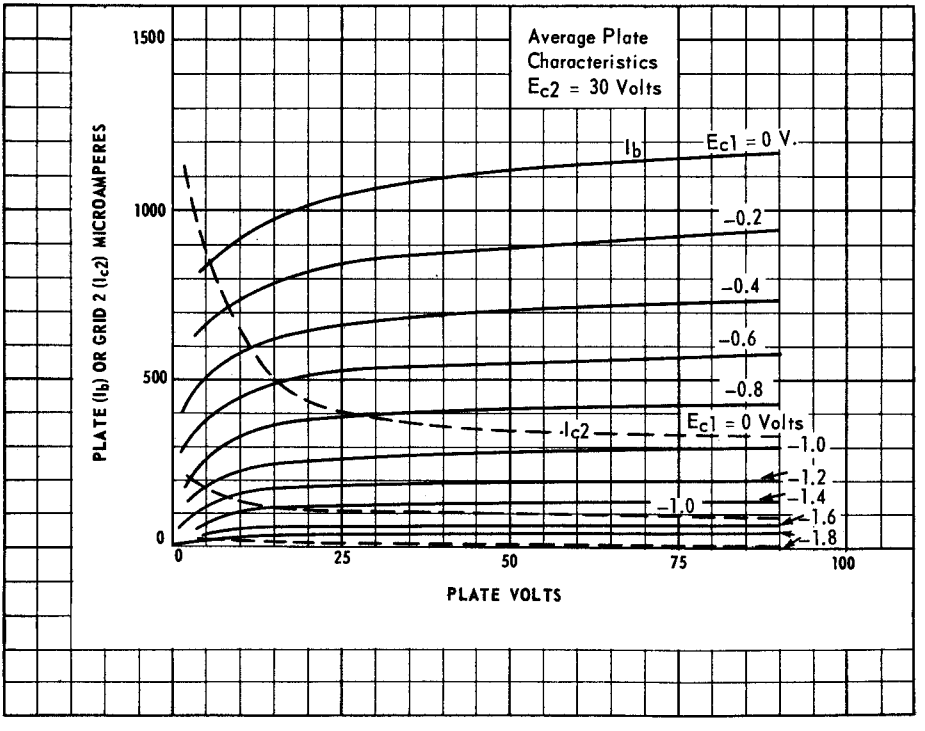
CONTINUED FROM PRECEDING PAGE

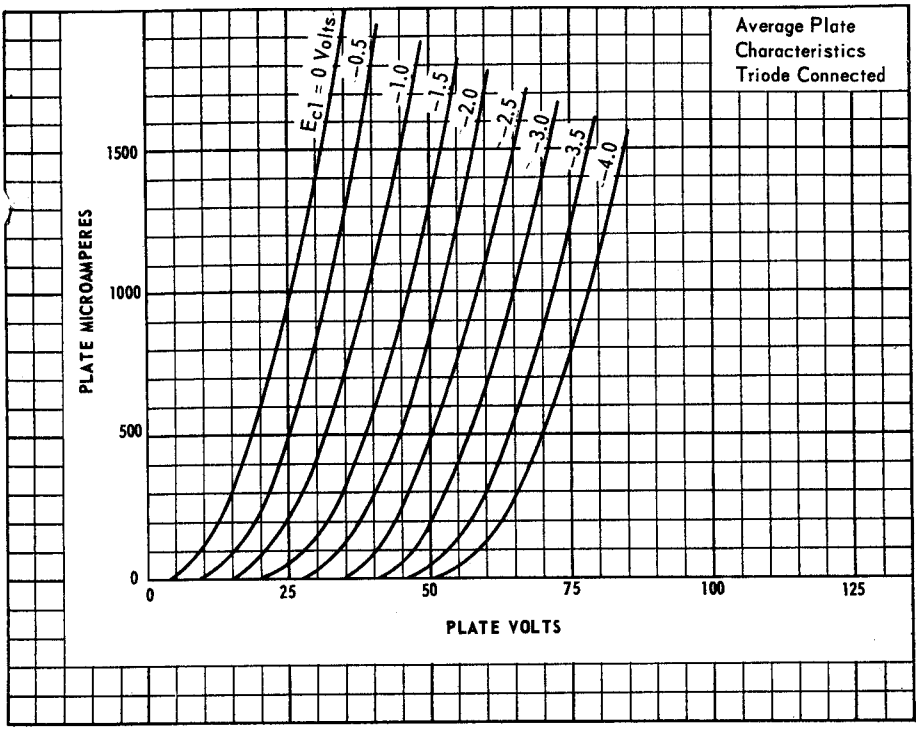
CHARACTERISTICS AND TYPICAL OPERATION

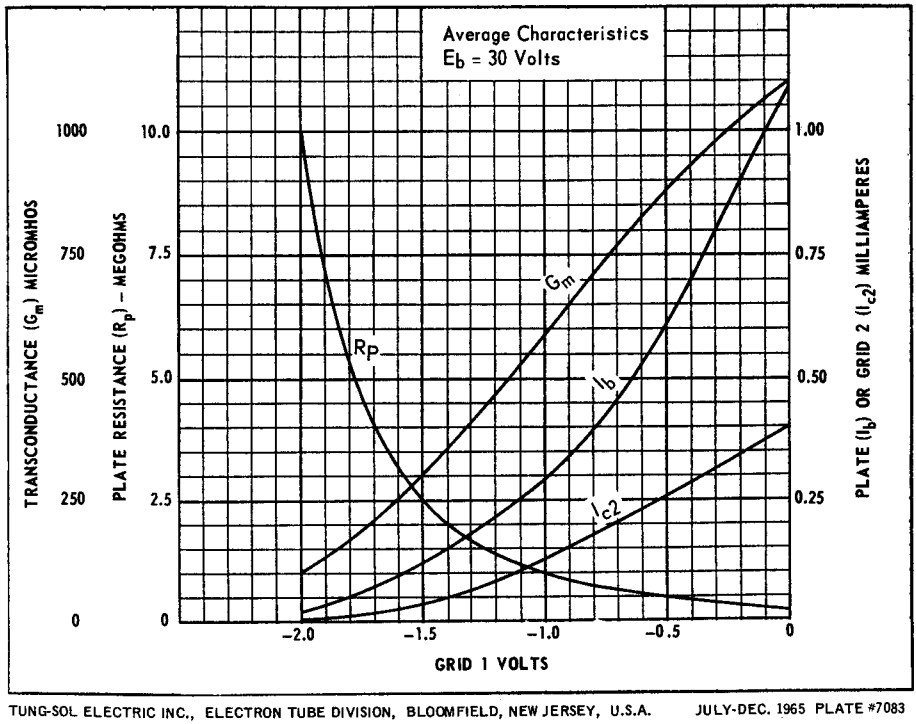
CLASS A_1 AMPLIFIER

PLATE VOLTAGE	30	45	VOLTS
GRID 2 VOLTAGE	30	*45	VOLTS
GRID 1 VOLTAGE (GRID RESISTOR = 5 MEGOHMS)	0	0	VOLTS
PLATE CURRENT	1.0	1.0	MA
GRID 2 CURRENT	0.35	0.35	MA
TRANSCONDUCTANCE	1,000	1,000	μMHOS
PLATE RESISTANCE – APPROX.	0.4	0.4	MEGOHM
GRID 1 VOLTAGE (APPROX.) FOR G_m = 10 μMHOS	–3.0	–	VOLTS

*GRID 2 SUPPLY VOLTAGE THROUGH SERIES 47,000 OHMS SUPPLY RESISTOR.




Average Plate
Characteristics
Triode Connected
E_{c1} = 0 Volts
-0.5
-1.0
-1.5
-2.0
-2.5
-3.0
-3.5
-4.0
PLATE MICROAMPERES
1500
1000
500
0
0
25
50
75
100
125
PLATE VOLTS


Average Characteristics
E_b = 30 Volts
TRANSCONDUCTANCE (G_m) MICROMHOS
1000
750
500
250
0
PLATE RESISTANCE (R_p) – MEGOHMS
10.0
7.5
5.0
2.5
0
PLATE (I_b) OR GRID 2 (I_{c2}) MILLIAMPERES
1.00
0.75
0.50
0.25
G_m
R_P
I_b
I_{c2}
-2.0
-1.5
-1.0
-0.5
0
GRID 1 VOLTS